

International
IR Rectifier

PD - 94360

IRFP32N50KS

SMPS MOSFET

HEXFET® Power MOSFET

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

V _{DSS}	R _{DS(on)} typ.	I _D
500V	0.135Ω	32A

Benefits

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- LOW R_{DS(on)}



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	32	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	20	
I _{DM}	Pulsed Drain Current ①	130	
P _D @ T _C = 25°C	Power Dissipation	460	W
	Linear Derating Factor	3.7	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	13	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw		

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy②	—	450	mJ
I _{AR}	Avalanche Current①	—	32	A
E _{AR}	Repetitive Avalanche Energy①	—	46	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	0.26	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.24	—	
R _{θJA}	Junction-to-Ambient	—	40	



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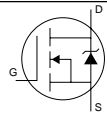
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.54	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.135	0.16	Ω	$V_{GS} = 10V, I_D = 32A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	250	μA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	14	—	—	S	$V_{DS} = 50V, I_D = 32A$
Q_g	Total Gate Charge	—	—	190	nC	$I_D = 32A$ $V_{DS} = 400V$ $V_{GS} = 10V$ ④
Q_{gs}	Gate-to-Source Charge	—	—	59		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	84		
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$V_{DD} = 250V$ $I_D = 32A$ $R_G = 4.3\Omega$ $V_{GS} = 10V$ ④
t_r	Rise Time	—	120	—		
$t_{d(off)}$	Turn-Off Delay Time	—	48	—		
t_f	Fall Time	—	54	—		
C_{iss}	Input Capacitance	—	5280	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V$ to $400V$ ⑤
C_{oss}	Output Capacitance	—	550	—		
C_{rss}	Reverse Transfer Capacitance	—	45	—		
C_{oss}	Output Capacitance	—	5630	—		
C_{oss}	Output Capacitance	—	155	—		
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	265	—		

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	32	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	130		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 32A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	530	800	ns	$T_J = 25^\circ\text{C}, I_F = 32A$
Q_{rr}	Reverse Recovery Charge	—	9.0	13.5	μC	$di/dt = 100A/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	30	—	A	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.87\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 32A$,
- ③ $I_{SD} \leq 32A$, $di/dt \leq 197A/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

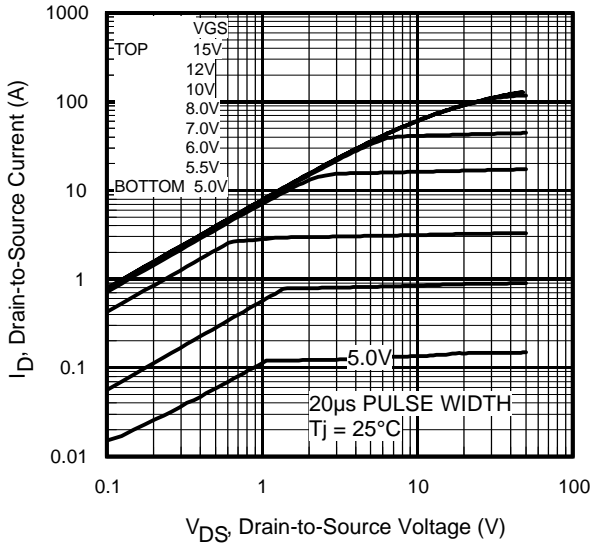


Fig 1. Typical Output Characteristics

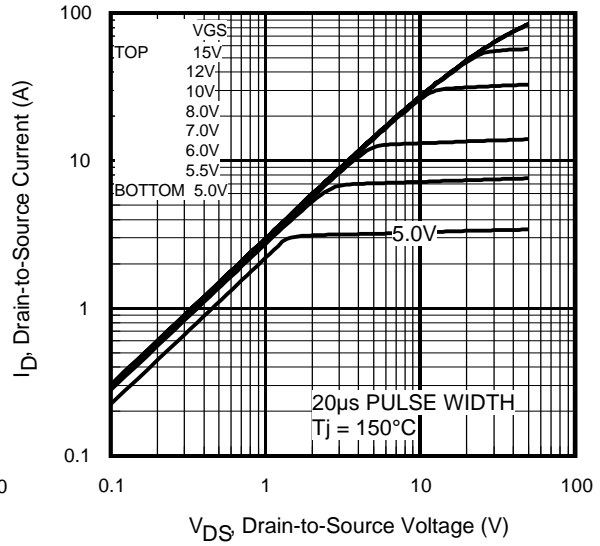


Fig 2. Typical Output Characteristics

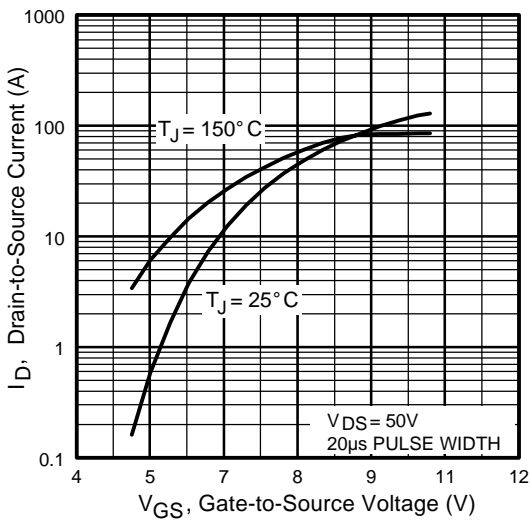


Fig 3. Typical Transfer Characteristics

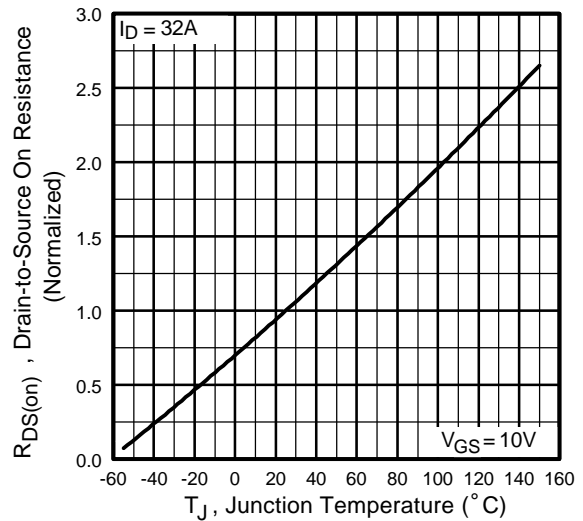


Fig 4. Normalized On-Resistance Vs. Temperature

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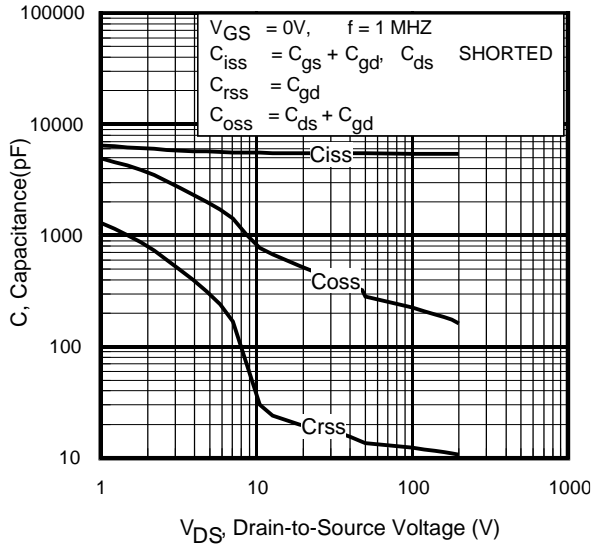


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

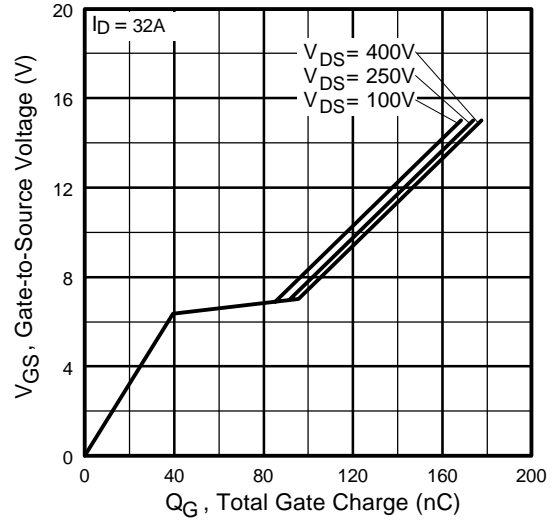


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

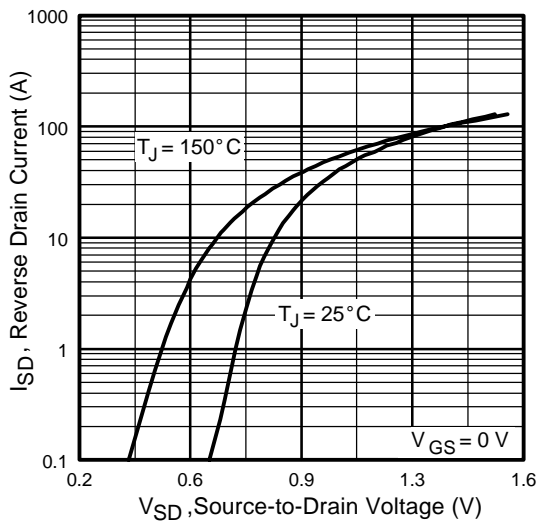


Fig 7. Typical Source-Drain Diode Forward Voltage

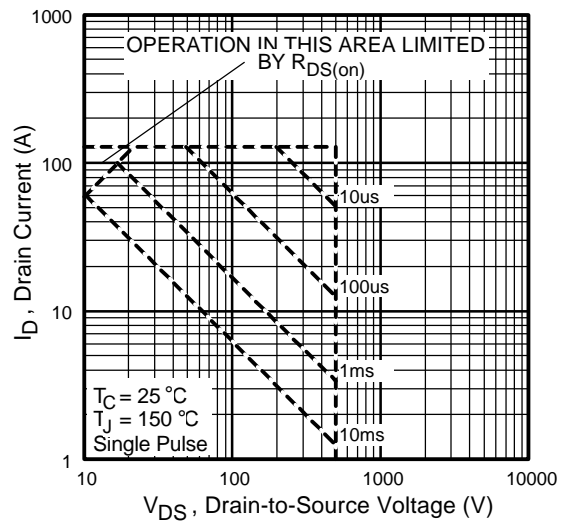


Fig 8. Maximum Safe Operating Area

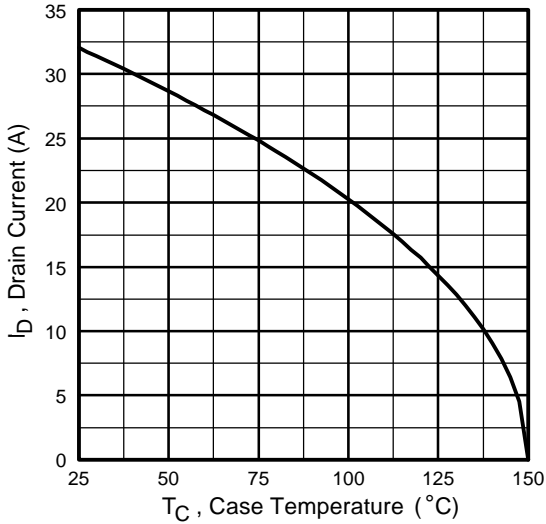


Fig 9. Maximum Drain Current Vs. Case Temperature

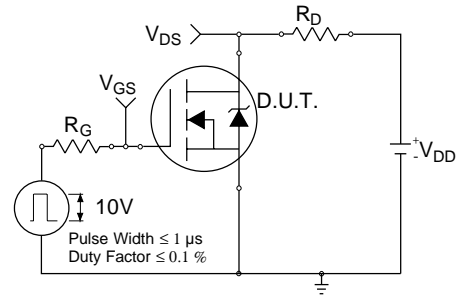


Fig 10a. Switching Time Test Circuit

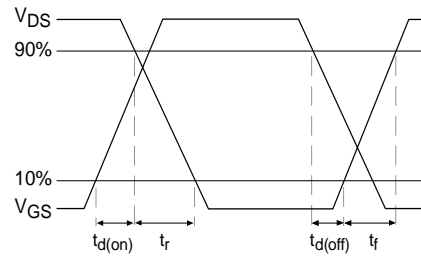


Fig 10b. Switching Time Waveforms

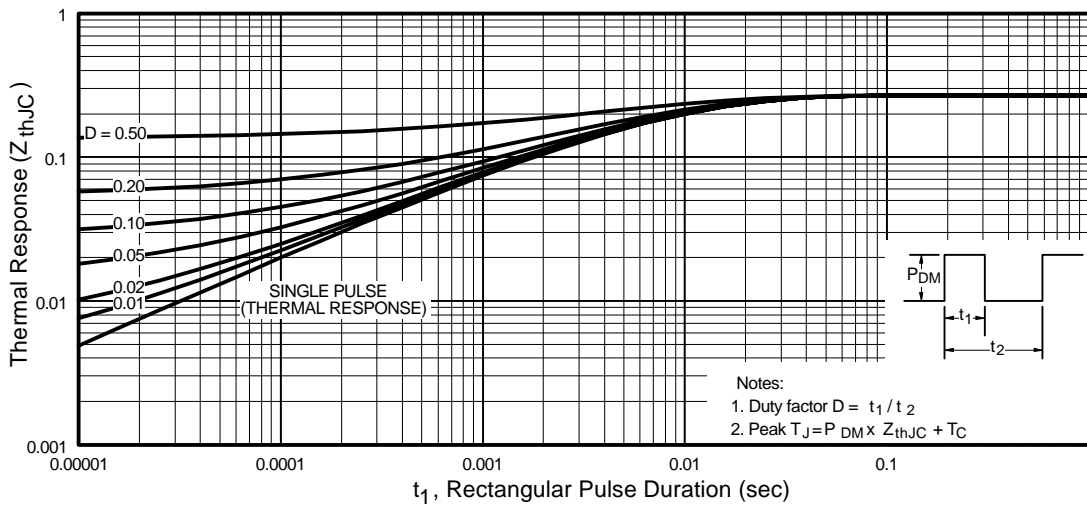


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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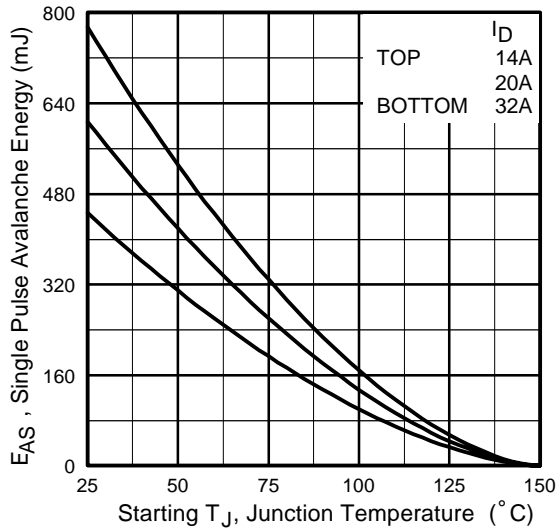


Fig 12a. Maximum Avalanche Energy Vs. Drain Current

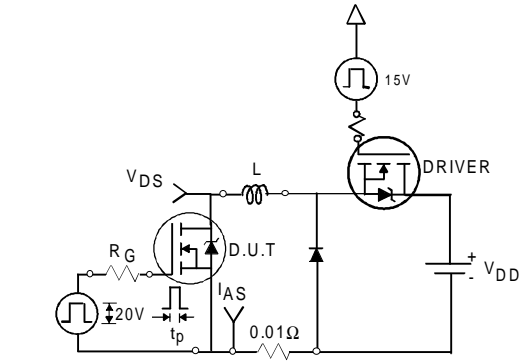


Fig 12c. Unclamped Inductive Test Circuit

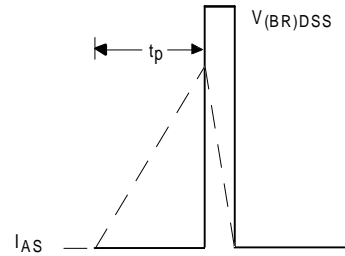


Fig 12d. Unclamped Inductive Waveforms

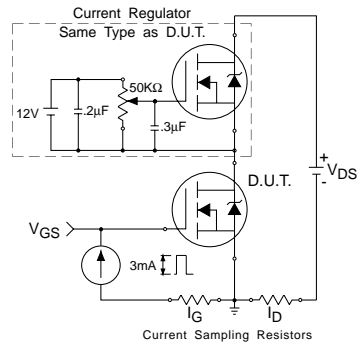


Fig 13a. Gate Charge Test Circuit

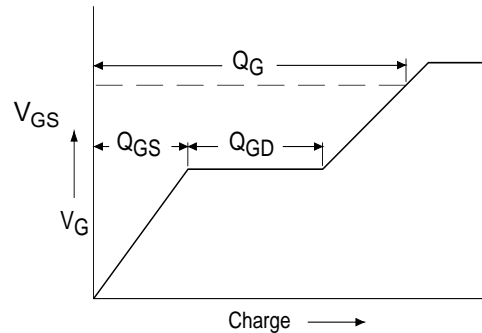
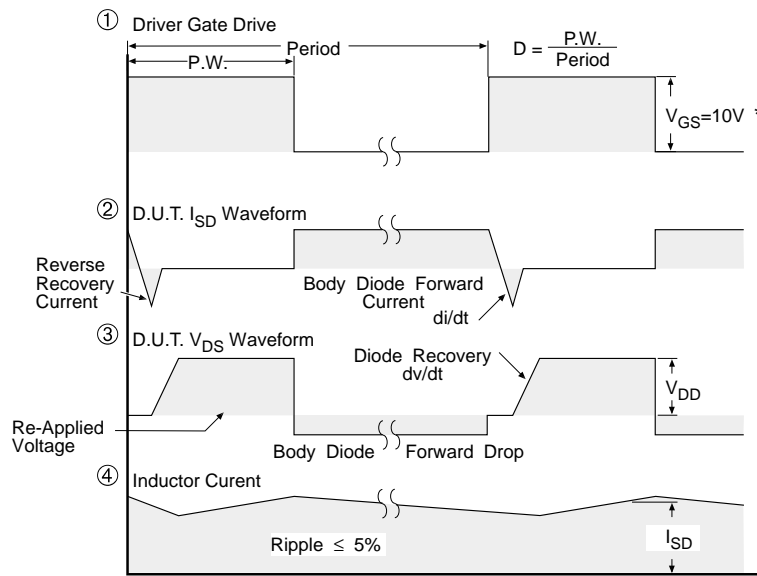
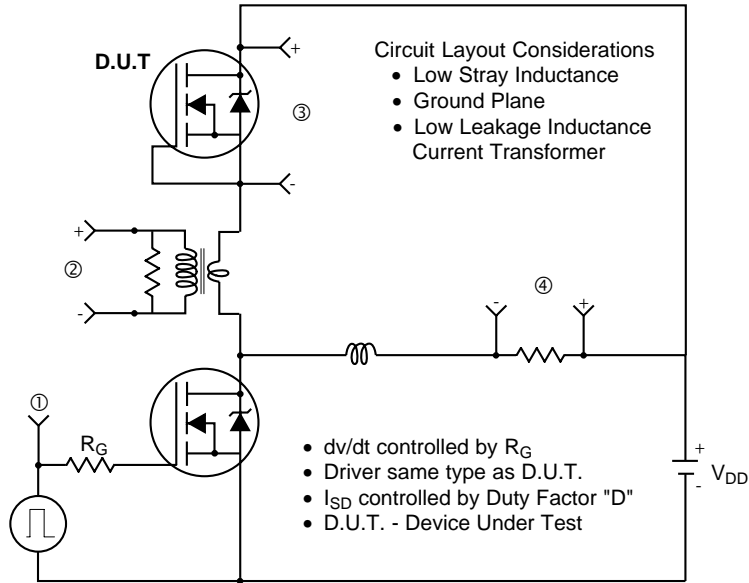


Fig 13b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



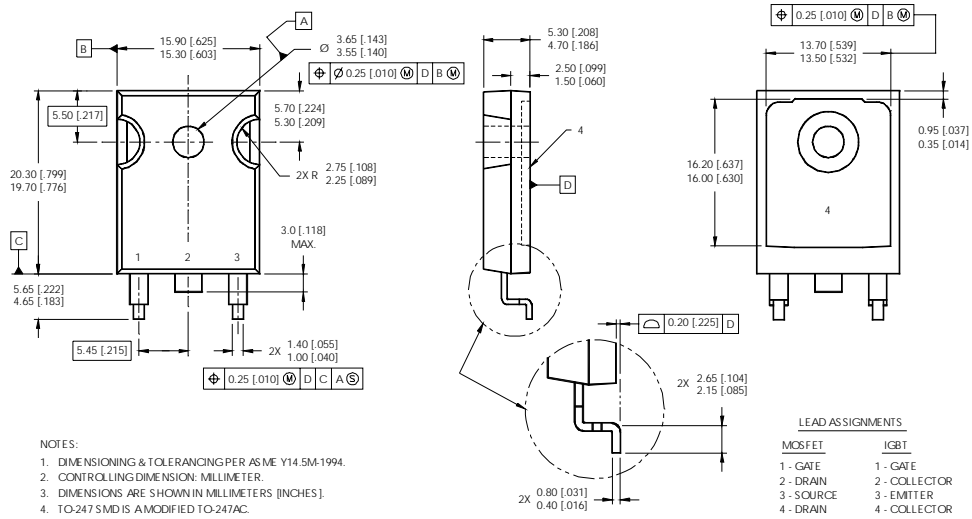
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

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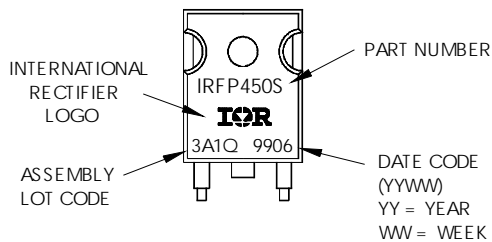
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SMD-247 Package Outline



SMD-247 Part Marking Information

EXAMPLE: THIS IS AN IRFP450S WITH
ASSEMBLY LOT CODE 3A1Q



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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